Listing of Claims:

1. (Currently Amended) A liquid crystal display comprising:

a plurality of gate lines (GØ - Gn) formed along a first direction;

a plurality of data lines (D1 - Dn) formed along a second direction substantially perpendicular to the first direction and crossing the gate lines;

a plurality of pixel electrodes each formed in a pixel area defined by the gate lines and the data lines, the pixel electrodes indicating pictures under control of the corresponding gate lines; and

a light ~~volume adjusting~~ transmission restricting layer formed ~~on a lower layer of~~ beneath the pixel electrodes ~~controlled by a second gate line (G1) among the gate lines~~.

2. (Currently Amended) The liquid crystal display as claimed in claim 1, wherein the light ~~volume adjusting~~ transmission restricting layer is ~~an active~~ a semiconductive layer.

3. (Currently Amended) The liquid crystal display as claimed in claim 2, wherein the ~~active~~ semiconductive layer is an amorphous silicon layer.

4. (Withdrawn) A method for manufacturing a liquid crystal display, the method comprising:

forming gate lines and a gate electrode on a substrate;

forming a gate insulating film on the substrate, including the gate electrode;

forming a first active layer on the gate insulating film corresponding to an upper portion of the gate electrode and forming a second active layer on the gate insulating film corresponding to a portion where pixel electrodes are to be formed;

forming source/drain electrodes on an upper portion of the first active layer; and

forming a passivation film on the whole surface of the active layer including the source/drain electrodes.

5. (Withdrawn) The method as claimed in claim 4, wherein the first and second active layers are amorphous silicon layers.

6. (Withdrawn) The method as claimed in claim 4, wherein a thickness of the second active layer is changed according to the transmission of light.

7. (Withdrawn) The method as claimed in claim 6, wherein the second active layer is adjusted in area according to an etching speed.

8. (Currently Amended) A liquid crystal display (LCD) device, comprising:

a substrate;

a plurality of scanning lines (GØ - Gn) extending along a first direction on the substrate;

a plurality of data lines (D1 - Dn) extending along a second direction substantially perpendicular to the first direction on the substrate and crossing the scanning lines (GØ - Gn);

a plurality of switching devices on the substrate arranged in a plurality of rows, each switching device connected to one of the scanning lines (GØ - Gn) for controlling a switching of the switching device and one of the data lines (D1 - Dn) for applying data to the switching device, wherein switching devices in each row are connected to a same scanning line, and wherein the rows of switching devices are sequentially scanned by the scanning lines (GØ - Gn);

a plurality of pixel electrodes on the substrate in a plurality of pixel areas defined by the scanning lines (GØ - Gn) and the data lines (D1 - Dn), the pixel electrodes each being connected to a corresponding one of the switching devices; and

a light transmission restricting layer formed ~~on the substrate~~ beneath the plurality of pixel electrodes, wherein the plurality of pixel electrodes are controlled by a second scanning line (G1) among the scanning lines (GØ - Gn).

9. (Currently Amended) The LCD device of claim 8, wherein the light transmission restricting layer is ~~an active~~ a semiconductive layer.

10. (Currently Amended) The LCD device of claim 9, wherein the switching devices include ~~a second~~ an active layer.

11. (Currently Amended) The LCD device of claim 9, wherein the ~~active~~ semiconductive layer is an amorphous silicon layer.

12. (Original) The LCD device of claim 8, further comprising an insulating material between the light transmission restricting layer and the substrate.

13. (Currently Amended) A method for manufacturing a liquid crystal display, the method comprising:

forming a plurality of scanning lines (GØ - Gn) along a first direction on a substrate;

forming an insulating layer on the substrate including the scanning lines (GØ - Gn);

forming a light transmission restricting layer on the insulating layer;

forming a plurality of data lines (D1 - Dn) along a second direction substantially perpendicular to the first direction on the substrate and crossing the scanning lines (GØ - Gn); and

forming a plurality of pixel electrodes on the substrate in a plurality of pixel areas defined by the scanning lines (GØ - Gn) and the data lines (D1 - Dn), the pixel electrodes each being controlled by one of the scanning lines,

wherein the light transmission restricting layer is formed beneath the plurality of pixel electrodes ~~controlled by a second scanning line (G1) among the scanning lines (GØ - Gn)~~.

14. (Original) The method of claim 13, further comprising forming a second insulating layer on the light transmission restricting layer before forming the pixel electrodes.

15. (Original) The method of claim 13, further comprising forming a plurality of switching devices on the substrate arranged in a plurality of rows, each switching device connected to one of the scanning lines (GØ - Gn) and one of the data lines (D1 - Dn).

16. (Original) The method of claim 13, wherein an active layer of the switching devices is formed while forming the light transmission restricting layer.

17. (New) The liquid crystal display as claimed in claim 1, wherein the light transmission restricting layer is formed beneath a plurality of pixel electrodes that are controlled by a second gate line (G1) among the gate lines (GØ - Gn).

18. (New) The method of claim 13, wherein the light transmission restricting layer is formed beneath the plurality of pixel electrodes that are controlled by a second scanning line (G1) among the scanning lines (GØ - Gn).